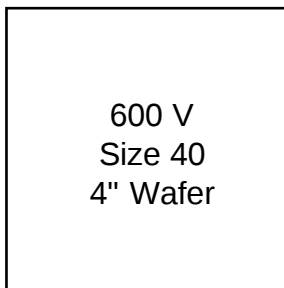


HF40A060ACB Hexfred Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
V_{FM}	Forward Voltage	1.6V Max.	$T_J = 25^{\circ}C$, $I_F = 10A$
BV_R	Reverse Breakdown Voltage	600V Min.	$T_J = 25^{\circ}C$, $I_R = 250\mu A$
I_{RM}	Reverse Leakage Current	20 μA Max.	$T_J = 25^{\circ}C$, $V_R = 600V$

Mechanical Data

Normal Backmetal Composition, Thickness:	Cr-Ni-Ag (1 kA-4kA-6kA)
Normal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.169" x 0.220"
Wafer Diameter:	100mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5162
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : HFA25TB60

Die Outline

INK DOT LOCATION 4.29 (.169) 5.29 (.220) 4.30 (.1694) 2.98 (.1175) ANODE	NOTES : - ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES) - CONTROLLING DIMENSION : (INCH) - LETTER DESIGNATION : S = SOURCE SK = SOURCE KELVIN G = GATE IS = CURRENT SENSE - DIMENSIONAL TOLERANCES BONDING PADS : < 0.635 TOLERANCE = +/- 0.013 WIDTH < (.0250) TOLERANCE = +/- (.0005) & > 0.635 TOLERANCE = +/- 0.025 LENGTH > (.0250) TOLERANCE = +/- (.0010) OVERALL DIE < 1.270 TOLERANCE = +/- 0.102 WIDTH < (.050) TOLERANCE = +/- (.004) & > 0.635 TOLERANCE = +/- 0.203 LENGTH > (.050) TOLERANCE = +/- (.008) - UNLESS OTHERWISE NOTED ALL DIE ARE GEN III
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